鼎德丰
DING DE FENG

NPN Silicon Transistor

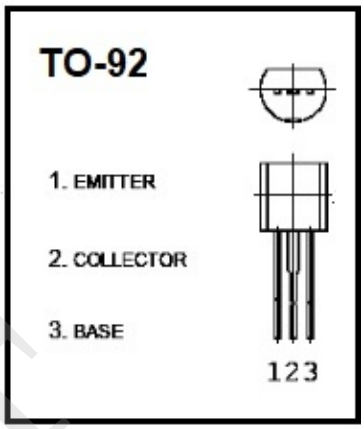
2SC3202

Features

- Complementary to 2SA1270
- Package:TO-92

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	35	V
Collector-emitter voltage	BV_{CEO}	30	V
Emitter-base voltage	BV_{EBO}	5	V
Collector current	I_{CM}	500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃



Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=50μA，I_E=0	35			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA，I_B=0	30			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=50μA，I_C=0	5			V
collector-base cut-off current	I_{CBO}	V_{CB}=35V，I_E=0			0.1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=5V，I_C=0			0.1	μA
DC current gain	H_{FE}	V_{CE}=1V，I_C=100mA	70		240	
		V_{CE}=6V，I_C=400mA	25			
collector-emitter saturation voltage	V_{CESAT}	I_C=100mA，I_B=10mA			0.25	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=100mA，I_B=10mA			1.0	
Transition frequency	f_T	V_{CE}=6V，I_C=20 mA	150	200		MH_Z
Output Capacitance	C_{ob}	V_{CE}=6V，I_C=0 mA, f=1MHz		7		pF

Classification of H_{FE}

Rank	O	Y
Range	70-140	120-240